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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/697,024	10/31/2003	Seung-Hee Nam	8733.895.00-US	1084	
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Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

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	Application No.	Applicant(s)	
Office Assistant Community	10/697,024	NAM ET AL.	
Office Action Summary	Examiner	Art Unit	
	Michael H. Caley	2871	
The MAILING DATE of this communication ap Period for Reply	pears on the cover sheet w	vith the correspondence address	
A SHORTENED STATUTORY PERIOD FOR REPL WHICHEVER IS LONGER, FROM THE MAILING D - Extensions of time may be available under the provisions of 37 CFR 1. after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailin earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUN 136(a). In no event, however, may a will apply and will expire SIX (6) MC e, cause the application to become A	ICATION. reply be timely filed NTHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133).	
Status		•	
1) Responsive to communication(s) filed on 19 J	<u>une</u> 2007.	•	
2a) This action is FINAL . 2b) ⊠ This	s action is non-final.		
3) Since this application is in condition for allowa	ince except for formal ma	tters, prosecution as to the merits is	
closed in accordance with the practice under	Ex parte Quayle, 1935 C.	D. 11, 453 O.G. 213.	
Disposition of Claims	·	•	
4) ☑ Claim(s) 1-19 and 21-23 is/are pending in the 4a) Of the above claim(s) 1-4 and 23 is/are wit 5) ☑ Claim(s) 18,19,21 and 22 is/are allowed. 6) ☑ Claim(s) 5-17 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/o	thdrawn from consideratio	n	
Application Papers			
9) ☐ The specification is objected to by the Examine 10) ☑ The drawing(s) filed on 08 December 2005 is/a Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) ☐ The oath or declaration is objected to by the E	are: a) \square accepted or b) [$\frac{1}{2}$ drawing(s) be held in abeyaction is required if the drawin	nce. See 37 CFR 1.85(a). g(s) is objected to. See 37 CFR 1.121(d)	I .
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documen 2. Certified copies of the priority documen 3. Copies of the certified copies of the priority documen application from the International Burea * See the attached detailed Office action for a list	ts have been received. ts have been received in ority documents have bee out (PCT Rule 17.2(a)).	Application No n received in this National Stage	
Attachment(s)		•	
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date	Paper No	Summary (PTO-413) (s)/Mail Date Informal Patent Application 	

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DETAILED ACTION

Continued Examination Under 37 CFR 1.114

A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 6/19/07 has been entered.

Claims 5-7 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lee (U.S. Patent Application Publication No. 2002/0071065) in view of Hoshino et al. (U.S. Patent Application Publication No. 2001/0050747 "Hoshino").

Regarding claim 5, Lee discloses a manufacturing method of an array substrate for a liquid crystal display device, comprising:

forming a gate electrode (Figure 8D element 102) on a substrate (Figure 8D element 100) having a display region (Figure 7);

forming a gate insulating layer (Figure 8D element 106) on the gate electrode; forming an active layer (Figure 8D element 108a) and an ohmic contact layer (Figure 8D element 108b) on the gate insulating layer over the gate electrode;

forming source (Figure 8D element 112) and drain (Figure 8D element 114) electrodes;

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forming a pixel electrode (Figure 7 elements 116 and 117) contacting the drain electrode on the gate insulating layer;

forming an alignment layer (Figure 8D element 118) on the pixel electrode and the source and drain electrodes, wherein the alignment layer directly contacts the pixel electrode and the source and drain electrodes (Figure 8D); and

forming a data line (Figure 7 element 113) connected to the source electrode.

Lee fails to disclose the steps of forming a data pad at a non-display region and forming a data pad terminal directly contacting an upper surface of the data pad as proposed. Hoshino, however, teaches forming a data pad (Figure 1 element 7, expanded dotted bottom pad portion) and a data pad terminal (Figures 1 and 3 element 20) contacting the data pad in the non-display region (Figures 1 and 3 element 3), the data pad terminal directly contacting and extending below a seal pattern (Figure 3 element 56) between the substrate and an opposing substrate (Figure 3).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to form the display device disclosed by Lee to have a data pad at the non-display region and a data pad terminal contacting the data pad, the data pad terminal directly contacting and extending below a seal pattern. One would have been motivated to provide a data pad and data pad terminal as proposed to provide a signal to the data line for controlling switching elements within the display region (Page 2 [0024]).

Regarding claims 6 and 7, Lee fails to disclose the data pad terminal and the pixel electrode as formed at the same time and as having the same material. Hoshino, however, teaches the data pad terminal as formed at the same time and of the same material as the pixel electrode (Page 3 [0038]).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to form the data pad terminal at the same time and of the same material as the pixel electrode. One would have been motivated to form the data pad terminal and the pixel electrode as proposed to benefit from a process using a reduced number of masks and manufacturing steps. As is known in the art, such a reduction in masking steps is beneficial to significantly reduce manufacturing costs and improve manufacturing yield.

Claim 8 is rejected under 35 U.S.C. 103(a) as being unpatentable over Lee in view of Hoshino and in further view of Matsunaga et al. (U.S. Patent No. 5,510,918 "Matsunaga").

Lee fails to disclose the pad terminal as extending to the display region. Matsunaga, however, teaches a pad terminal less susceptible to corrosion by extending the pad terminal to the display region beneath a passivation layer (Figures 8 and 19 element DTM; Column 12 lines 19-30).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to have formed the pad terminal disclosed by Lee to extend to the display region. One would have been motivated to extend the pad terminal to the display region to keep the resistance of the data terminal from increasing due to corrosion (Column 12 lines 26-30).

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Claim 9 is rejected under 35 U.S.C. 103(a) as being unpatentable over Lee in view of Hoshino and in further view of Park et al. (U.S. Patent Application Publication No. 2002/0074549 "Park").

Regarding claim 9, Lee fails to explicitly disclose at least one of the electrodes as formed by a dry etching method. Park, however, teaches a dry-etching process as advantageous for forming multiple display layers simultaneously (Page 7 [0127]-[0129]).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to form at least one of the display electrodes from a dry-etching process. One would have been motivated to use the dry-etching process to reduce the number of steps in forming the TFT structures in the display device by forming multiple layers simultaneously and thus reduce manufacturing costs (Page 7 [0127]-[0129]).

Claims 10, 11, 13, and 14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lee in view of Hoshino and in further view of Tanaka et al. (U.S. Patent Application Publication No. 2001/0035527 "Tanaka").

Regarding claims 10 and 13, Lee fails to disclose one of the electrodes or ohmic contact layer as formed by a photolithography method using a photoresist. Tanaka, however, teaches a photolithography method using a photoresist to form at least one of the electrodes and the ohmic contact layer (Page 4 [0070], [0073], Page 5 [0075], [0080]) as part of a method of finely forming TFT and pixel electrode elements on a substrate (Page 1 [0004]).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to have formed at least one of the electrodes and the ohmic contact layer in the display

device disclosed by Lee by a photolithography method using a photoresist. Tanaka teaches such a method as conventionally used to finely form display elements on the active matrix substrate (Page 1 [0004]). One would have been motivated to use such a technique to benefit from the ability to finely control the placement of the TFT elements at a high density according to conventional methods.

Regarding claims 11 and 14, Lee fails to disclose the photoresist used in the photolithography method as removed by a dry strip method (ashing). Tanaka, however, teaches such a photoresist removal method as beneficial to enable a reduction in the number of photolithography steps in forming the TFT electrodes and ohmic contact layer (Page 2 [0011]-[0013], Page 4 [0073], [0074], Page 6 [0086]).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to remove the photoresist by a dry strip method in the display device disclosed by Dohjo. One would have been motivated to apply such a method to reduce the number of photolithography steps (Page 2 [0011]-[0013]) and to configure the lateral dimensions of the layers such that impurities in the liquid crystal layer are prevented from entering the a-Si film (Page 6 [0086]).

Claim 12 is rejected under 35 U.S.C. 103(a) as being unpatentable over Lee in view of Hoshino and Tanaka and in further view of Okutani (U.S. Patent No. 5,135,608 "Okutani").

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Lee as modified by Tanaka discloses the dry strip method as using dry gases, but fails to disclose the use of O_2 as a base gas and SF_6 or CF_4 as a reactive gas. Okutani, however, teaches a mixture of CF_4 and O_2 as an alternative dry gas to O_2 alone in a dry strip method (Column 5 lines 10-15).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to have used O_2 as a base gas and SF_6 or CF_4 as a reactive gas in the dry strip method. One would have been motivated to use such a dry gas mixture as an engineering expediency to achieve the expected results of such a mixture such as a particular photoresist removal rate.

Claims 15 and 16 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lee in view of Hoshino and Tanaka and in further view of Nakamura et al. (U.S. Patent No. 6,621,537 "Nakamura").

Lee as modified by Tanaka fails to disclose the upper surface of the ohmic contact layer as etched to a depth between about 100 and about 700 Angstroms. Nakamura, however, teaches an etched ohmic contact film with a controllable thickness between 200 and 700 Angstroms (Column 8 lines 35-64).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to have formed the ohmic contact layer to have an etched thickness between 100 and 700 Angstroms and a thickness before etching of 400 and 1000 Angstroms. One would have been motivated to set the thickness before etching and the etched thickness as proposed to allow for controllability of the ohmic contact layer thickness according to a desired ON current for the TFT device (Column 8 lines 35-38).

Claim 17 is rejected under 35 U.S.C. 103(a) as being unpatentable over Lee in view

of Hoshino and in further view of Choi (U.S. Patent No. 6,169,592).

Lee fails to disclose the alignment layer as formed by a printing method. Choi, however, teaches the alignment layer as formed by a printing method (Column 2 line 10 – Column 3 line 16).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to have constructed the alignment layer disclosed by Lee by means of a printing method. One would have been motivated to form the alignment layer by a printing method as taught by Choi to avoid the labor intensive processes of alternative alignment layer forming methods (Column 2 lines 13-15) while forming a display having satisfactory display characteristics (Column 2 lines 36-49).

Allowable Subject Matter

Claims 18, 19, 21, and 22 are allowed.

The following is a statement of reasons for the indication of allowable subject matter:

Arguments presented on pages 9-10 of Remarks filed on 11/22/06 are persuasive in overcoming the rejection of claim 18. Specifically, arguments are persuasive in identifying that the prior art fails to disclose or suggest the method of manufacturing an array substrate for a liquid crystal display device in which an ohmic contact layer is etched by a dry etching process in a chamber, photoresist used in the formation of the ohmic contact layer is removed by a dry

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strip method in the chamber, and an upper surface of the ohmic contact layer is etched after the dry strip method.

Response to Arguments

Applicant's arguments with respect to claims 5-17 have been considered but are moot in view of the new ground(s) of rejection.

Contact Information

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Michael H. Caley whose telephone number is (571) 272-2286. The examiner can normally be reached on M-F 8:30 a.m. - 5:00 p.m..

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David C. Nelms can be reached on (571) 272-1787. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Michael H. Caley

September 2007